

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (L²-π-MOSV)

2SJ377

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

RELAY DRIVE, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- 4V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.16\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = -100\mu A$ (Max.) ($V_{DS} = -60V$)
- Enhancement-Mode : $V_{th} = -0.8 \sim -2.0V$
($V_{DS} = -10V$, $I_D = -1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	-60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	-60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	-5	A
	Pulse	I_{DP}	-20	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	20	W
Single Pulse Avalanche Energy**		E_{AS}	273	mJ
Avalanche Current		I_{AR}	-5	A
Repetitive Avalanche Energy*		E_{AR}	2	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	6.25	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	125	$^\circ C/W$

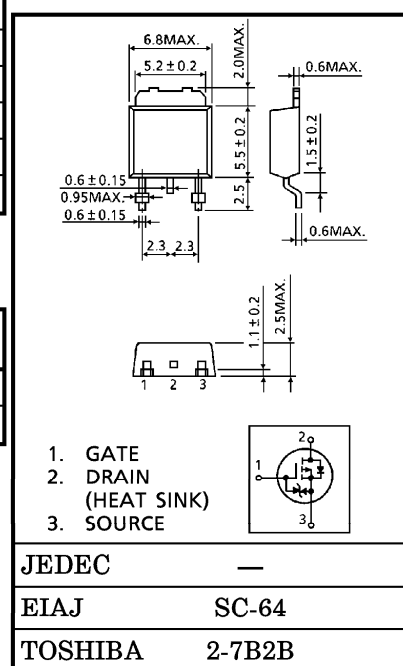
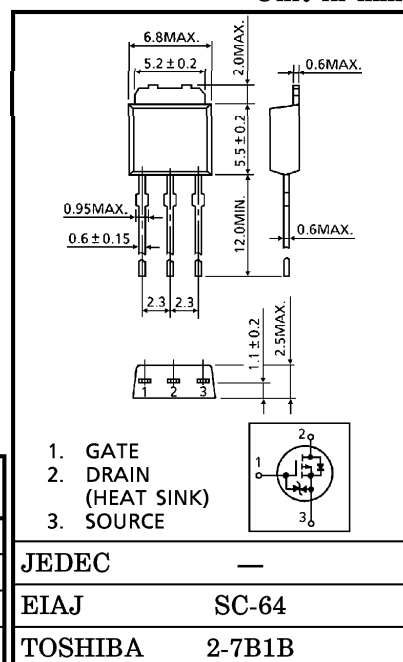
Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = -25V$, Starting $T_{ch} = 25^\circ C$, $L = 14.84mH$,
 $R_G = 25\Omega$, $I_{AR} = -5A$ This transistor is an electrostatic sensitive device.
Please handle with caution.

INDUSTRIAL APPLICATIONS

Unit in mm

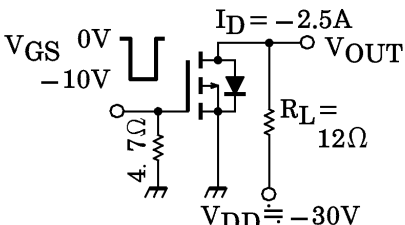


Weight : 0.35g

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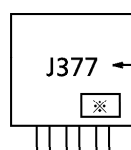
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$	—	—	± 10	μA
Drain Cut-off Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$	—	—	-100	μA
Drain-Source Breakdown Voltage	$V_{(BR) DSS}$	$I_D = -10mA, V_{GS} = 0V$	-60	—	—	V
Gate Threshold Voltage	V_{th}	$V_{DS} = -10V, I_D = -1mA$	-0.8	—	-2.0	V
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = -4V, I_D = -2.5A$	—	0.24	0.28	Ω
		$V_{GS} = -10V, I_D = -2.5A$	—	0.16	0.19	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -2.5A$	2.0	4.0	—	S
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V$ $f = 1MHz$	—	630	—	pF
Reverse Transfer Capacitance	C_{rss}		—	95	—	
Output Capacitance	C_{oss}		—	290	—	
Switching Time	Rise Time		—	25	—	ns
	Turn-on Time		—	45	—	
	Fall Time		—	55	—	
	Turn-off Time		—	200	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} = -48V, V_{GS} = -10V$ $I_D = -5A$	—	22	—	nC
Gate-Source Charge	Q_{gs}		—	16	—	
Gate-Drain ("Miller") Charge	Q_{gd}		—	6	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	-5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	-20	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = -5A, V_{GS} = 0V$	—	—	1.7	V
Reverse Recovery Time	t_{rr}	$I_{DR} = -5A, V_{GS} = 0V$	—	80	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR} / dt = 50A / \mu s$	—	0.1	—	μC

MARKING



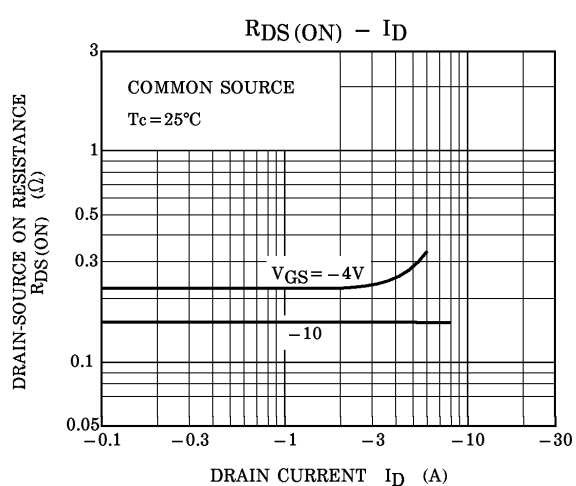
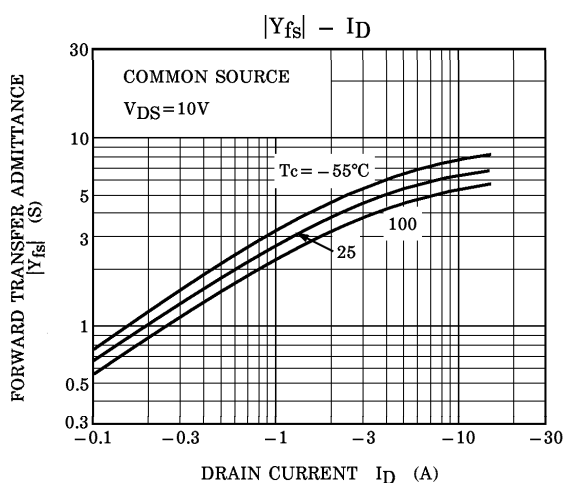
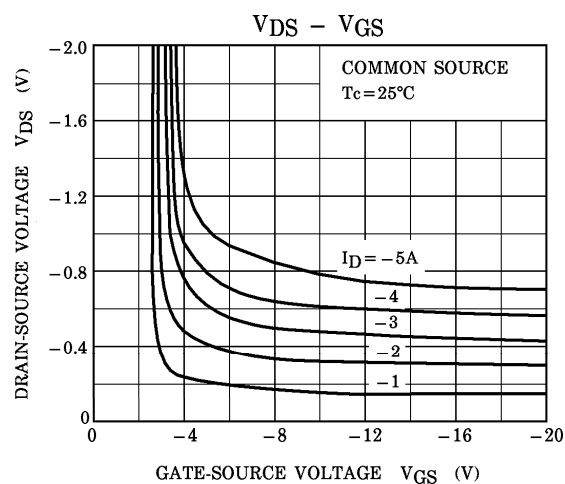
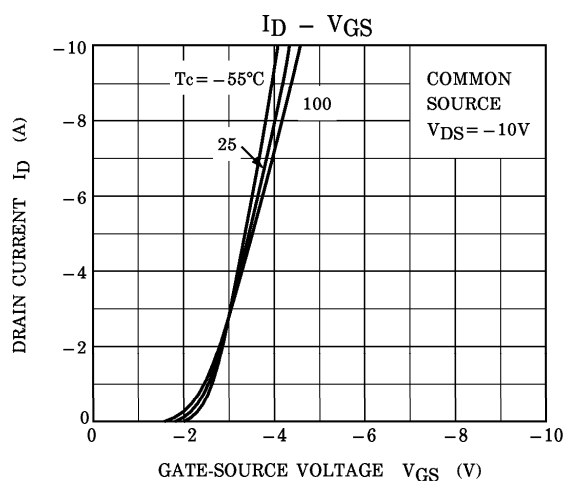
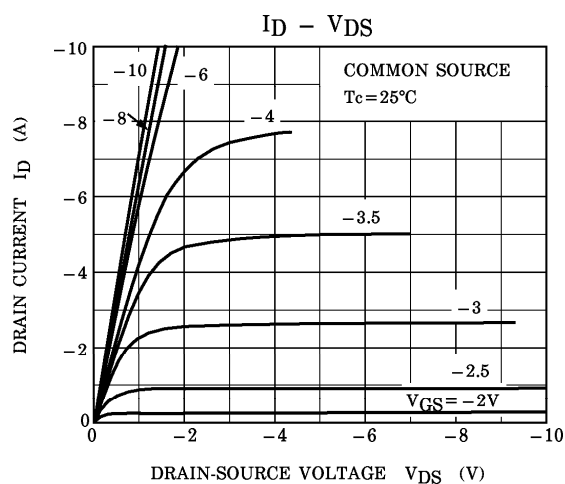
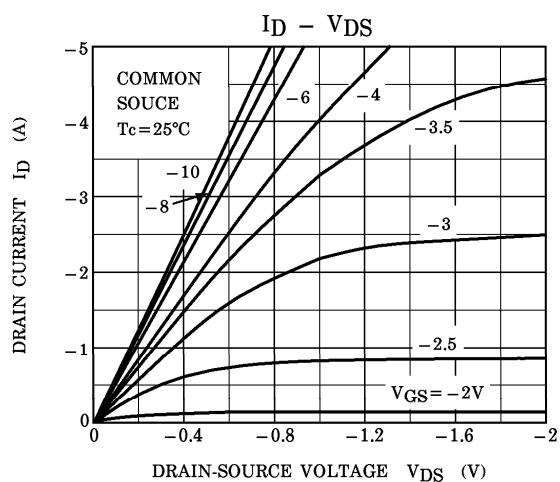
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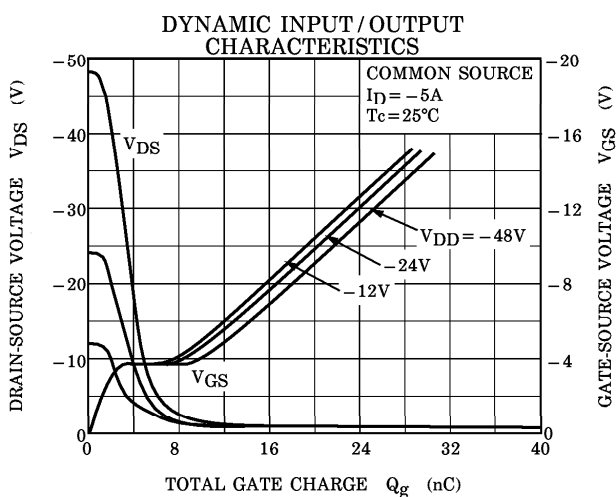
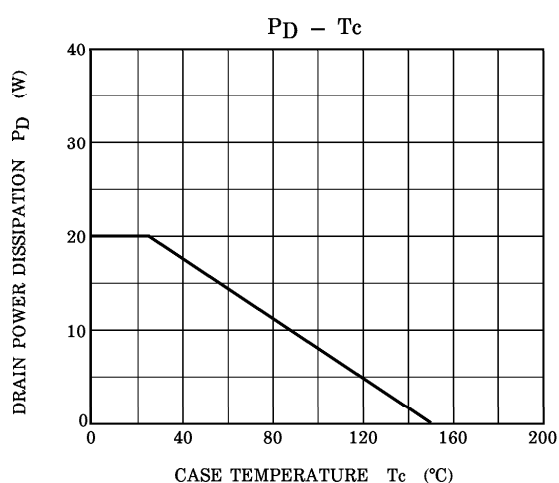
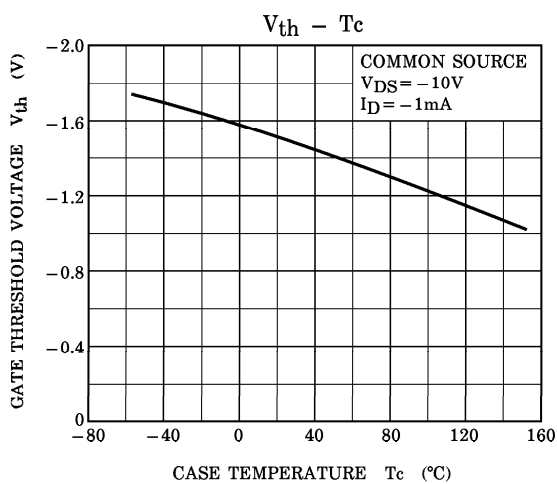
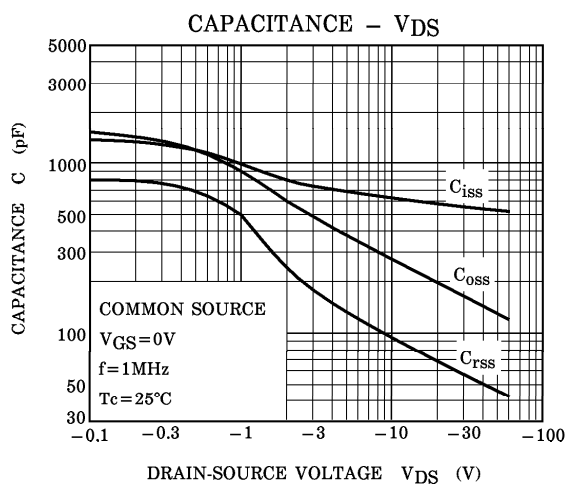
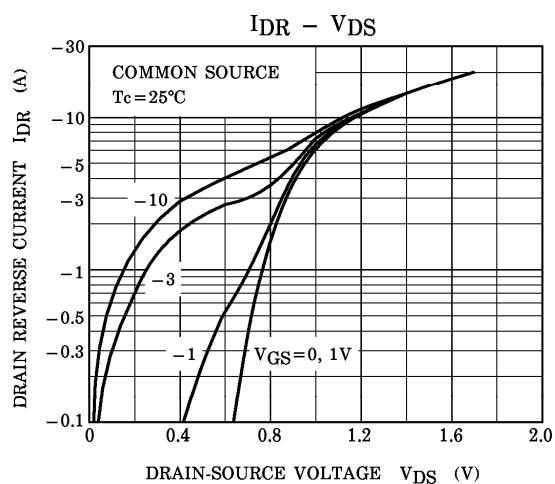
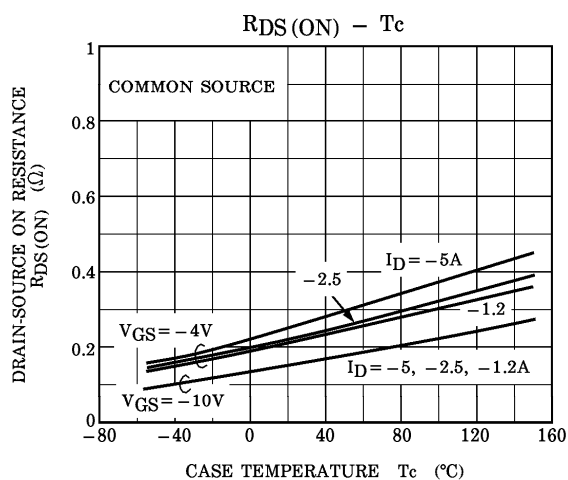
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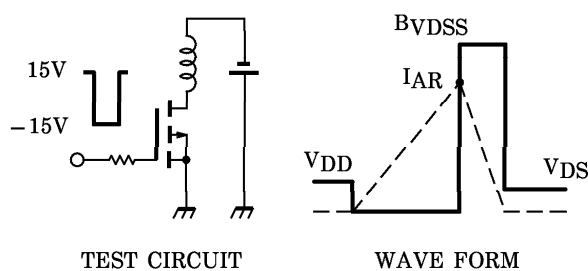
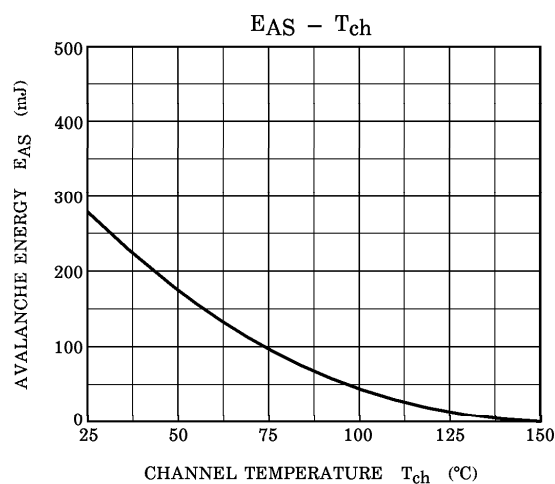
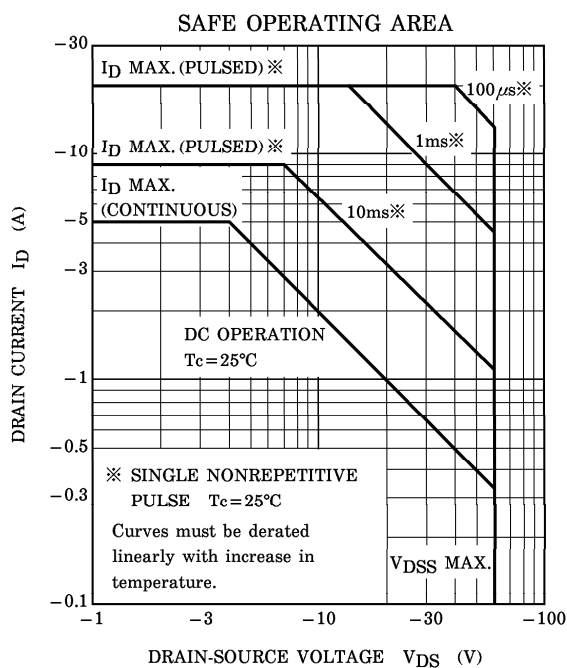
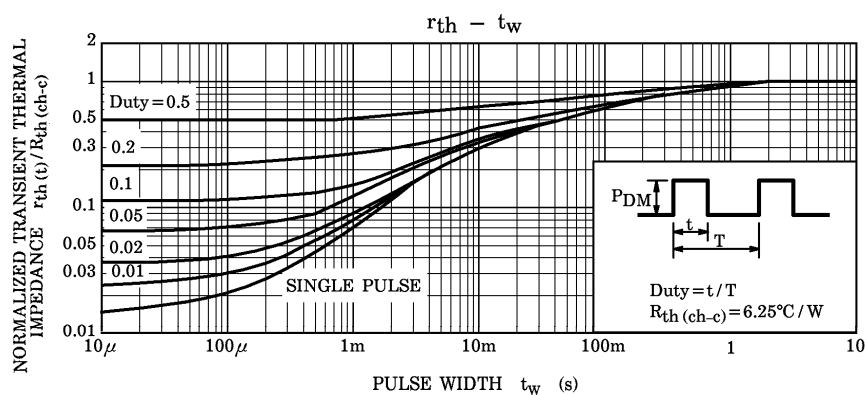


Month (Starting from Alphabet A)

Year (Last Number of the Christian Era)







Peak $I_{AR} = -5A$, $R_G = 25\Omega$
 $V_{DD} = -25V$, $L = 14.84mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$